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Defects in SemiConductors

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Need for solar cells: space research, oil crisis, cleaner energy, stabler energy

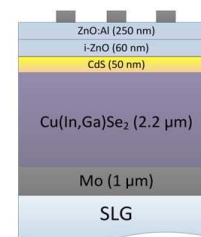
Evolution towards thin film:

Si solar cell absorbs relatively poor \rightarrow thick absorber needed ($\sim 100 \mu\text{m}$)



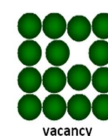
CuInGaSe₂ material has high absorption coefficient \rightarrow thin absorber ($\sim 2 \mu\text{m}$)

Advantage: lower cost, flexible cell

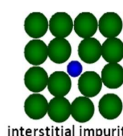


Problem: defects in absorber lattice reduce efficiency

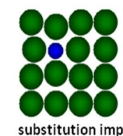
\rightarrow Research DiSC: defect characterization



vacancy



interstitial impurity

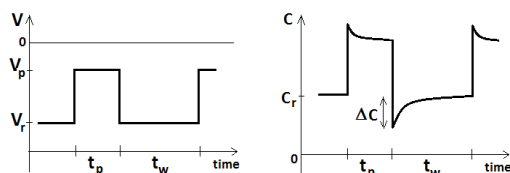


substitution impurity

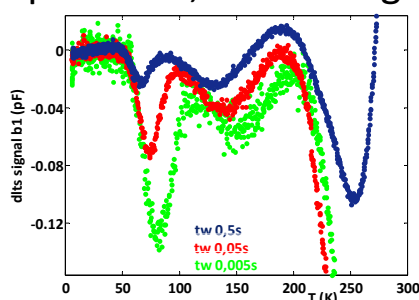
Research methods:

Deep Level Transient Spectroscopy

\rightarrow measure capacitance transient after voltage pulse for different temperature

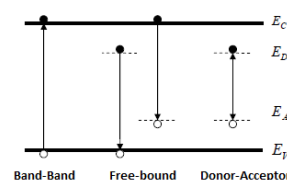


\rightarrow deep defects, contact signal

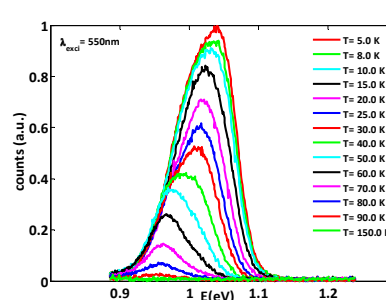


Photoluminescence

\rightarrow measure light of radiative recombination when cell is illuminated



\rightarrow shallow defects



Conclusion: by controlling defects in thin film solar cells the efficiency can be enhanced.